Dr. Dilder Chowdhury, Nexperia

Dilder Chowdhury is the GaN Device architect for Power GaN Technology at Nexperia. He has worked at Nexperia (formerly NXP Semiconductors & Philips Semiconductors) since 1996 and his career there has involved a wide spectrum of power devices ranging from high voltage BJT, DMOS and GaN HEMTs, to low voltage trench MOSFETs and mixed signal ICs for Power Management. As Device and Technology Architect of the Power GaN Technology group, he is currently responsible for developing next generation Power GaN FETs with focus on voltages from 650V to 1200V. His research interests involve optimizing both technology and design to specific applications, which arose from deep understanding of application specific parametric optimization in power management applications.

Dilder was awarded PhD in Semiconductor Device Technology (based on Super lattice structure) in III-V Semiconductors at The University of Manchester in 1995. He received his M.Sc Engineering and B.Sc Engineering degree from BUET. He is serving as patent review committee and peer reviewed many papers. He is currently a Fellow of the Royal Society.